Table 1. The average values of MOS capacitor with and without irradiation.

SiC MOS devices	V_{FB} (V)	Hysteresis	Leakage Current (A)
As-fabricated	-2.0±0.13	0.05±0.04	297±34
Post-irradiation	-2.33±0.37	0.36±0.32	201±92